



STD1NK60 - STD1NK60-1 STQ1HNK60R - STN1HNK60

N-CHANNEL 600V - 8Ω - 1A DPAK/TO-92/IPAK/SOT-223
 SuperMESH™ MOSFET

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STD1NK60	600 V	< 8.5 Ω	1 A	30 W
STD1NK60-1	600 V	< 8.5 Ω	1 A	30 W
STQ1HNK60R	600 V	< 8.5 Ω	0.4 A	3 W
STN1HNK60	600 V	< 8.5 Ω	0.4 A	3.3 W

- TYPICAL R_{DS(on)} = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ESD IMPROVED CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- LOW POWER BATTERY CHARGERS
- SWITCH MODE LOW POWER SUPPLIES(SMPS)
- LOW POWER, BALLAST, CFL (COMPACT FLUORESCENT LAMPS)

Figure 1: Package

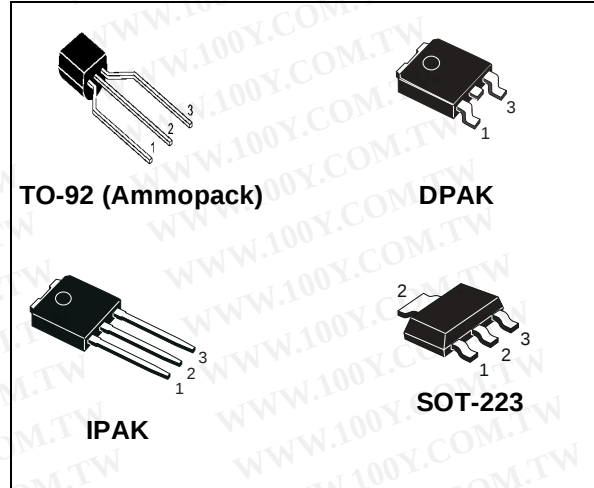


Figure 2: Internal Schematic Diagram

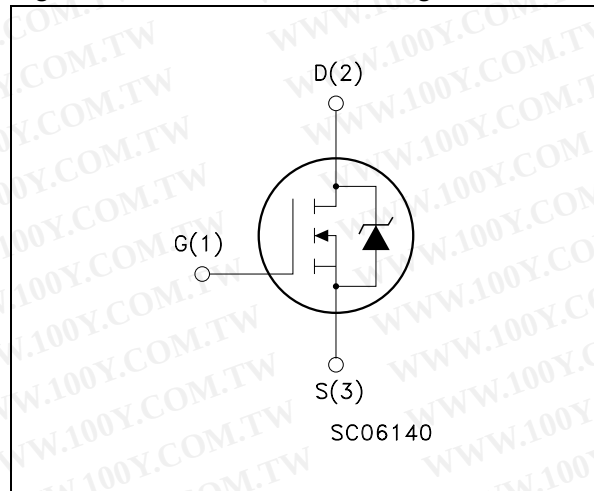


Table 2: Order Codes

Part Number	Marking	Package	Packaging
STD1NK60T4	D1NK60	DPAK	TAPE & REEL
STD1NK60-1	D1NK60	IPAK	TUBE
STQ1HNK60R	1HNK60R	TO-92	BULK
STQ1HNK60R-AP	1HNK60R	TO-92	AMMOPAK
STN1HNK60	N1HNK60	SOT-223	TAPE & REEL

Rev. 3

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Table 3: Absolute Maximum ratings

Symbol	Parameter	Value			Unit
		DPAK / IPAK	TO-92	SOT-223	
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	600			V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	600			V
V_{GS}	Gate- source Voltage	± 30			V
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	1.0	0.4	0.4	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	0.63	0.25	0.25	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	4	1.6	1.6	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	30	3	3.3	W
	Derating Factor	0.24	0.025	0.025	W/°C
$dv/dt(1)$	Peak Diode Recovery voltage slope	3			V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150			°C

(●) Pulse width limited by safe operating area

(1) $I_{SD} \leq 1.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{jMAX}$.

Table 4: Thermal Data

		DPAK/IPAK	TO-92	SOT-223	Unit
$R_{thj-case}$	Thermal Resistance Junction-case Max	4.16	--	--	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	100	120	37.87 (#)	°C/W
$R_{thj-lead}$	Thermal Resistance Junction-lead Max	--	40	--	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	275	260		°C

(#) When mounted on FR-4 board of 1 in², 2oz Cu, $t < 10\text{ sec}$

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	1	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	25	mJ

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

Table 6: On/Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.25	3	3.7	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 0.5\text{ A}$		8	8.5	Ω

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ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 15\text{ V}$, $I_D = 0.5\text{ A}$		1		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		156		pF
C_{oss}	Output Capacitance			23.5		pF
C_{rss}	Reverse Transfer Capacitance			3.8		pF
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 300\text{ V}$, $I_D = 0.5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 21)		6.5		ns
t_r	Rise Time			5		ns
$t_{d(off)}$	Turn-off Delay Time			19		ns
t_f	Fall Time			25		ns
Q_g	Total Gate Charge			7	10	nC
Q_{gs}	Gate-Source Charge	$V_{DD} = 480\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\text{ }\Omega$ (see, Figure 23)		1.1		nC
Q_{gd}	Gate-Drain Charge			3.7		nC

Table 8: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				1	A
I_{SDM} (2)	Source-drain Current (pulsed)				4	A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 1.0\text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 1.0\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$, $T_j = 25^\circ\text{C}$ (see test circuit, Figure 22)		140		ns
Q_{rr}	Reverse Recovery Charge			240		μC
I_{RRM}	Reverse Recovery Current			3.3		A
t_{rr}	Reverse Recovery Time	$I_{SD} = 1.0\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 22)		229		ns
Q_{rr}	Reverse Recovery Charge			377		μC
I_{RRM}	Reverse Recovery Current			3.3		A

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

Figure 3: Safe Operating Area For SOT-223

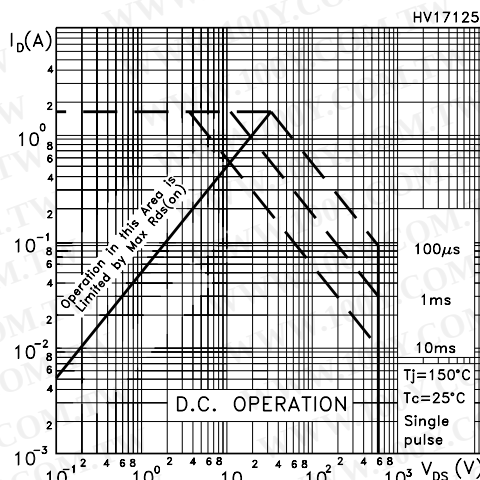


Figure 6: Thermal Impedance For SOT-223

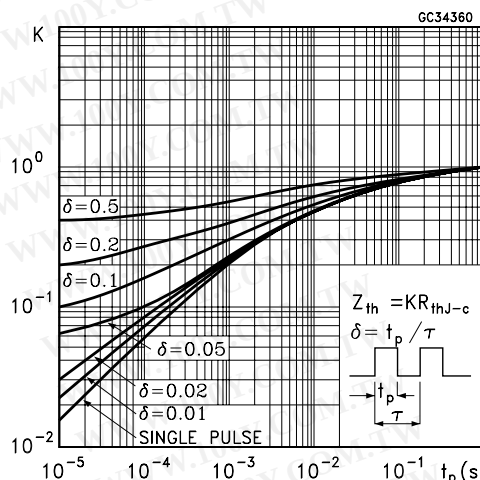


Figure 4: Safe Operating Area For DPAK/IPAK

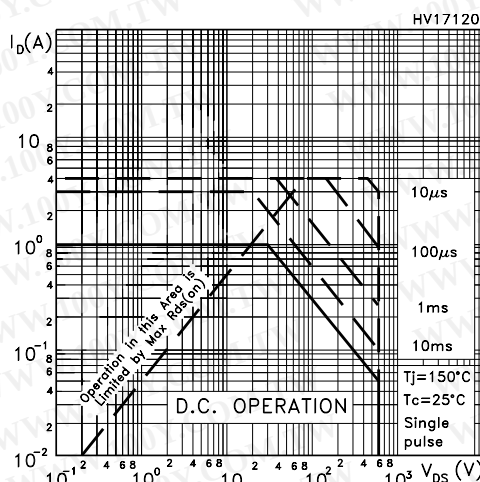


Figure 7: Thermal Impedance For DPAK/IPAK

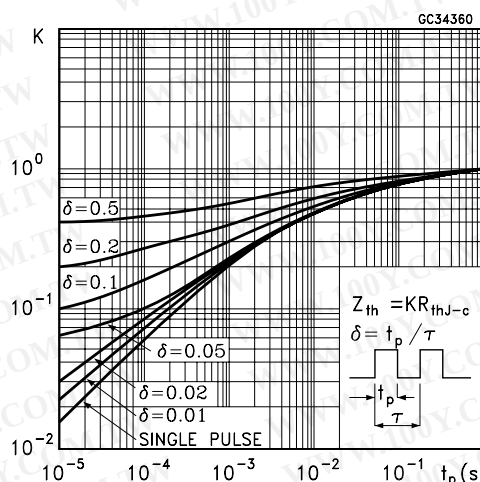


Figure 5: Safe Operating Area For TO-92

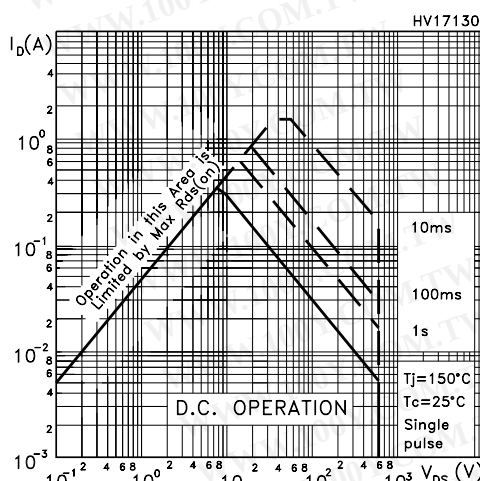


Figure 8: Thermal Impedance For TO-92

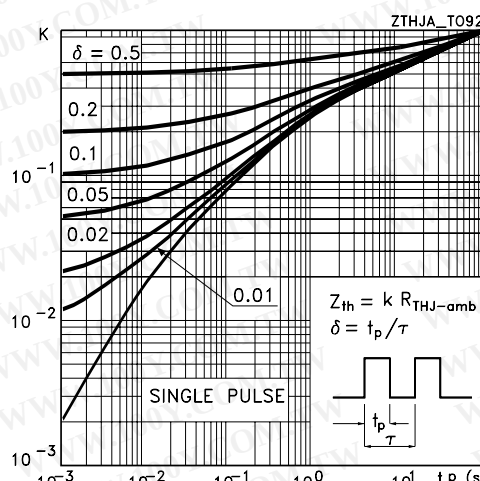


Figure 9: Output Characteristics

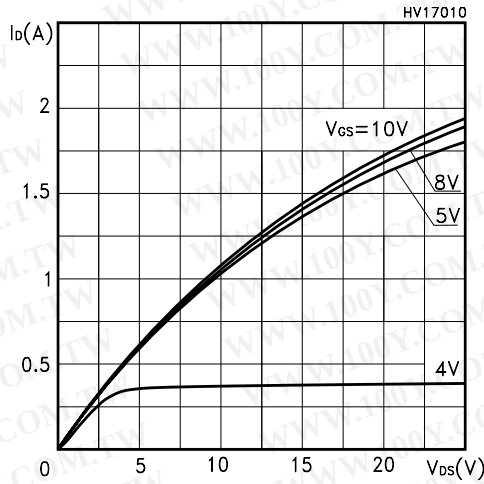


Figure 10: Transconductance

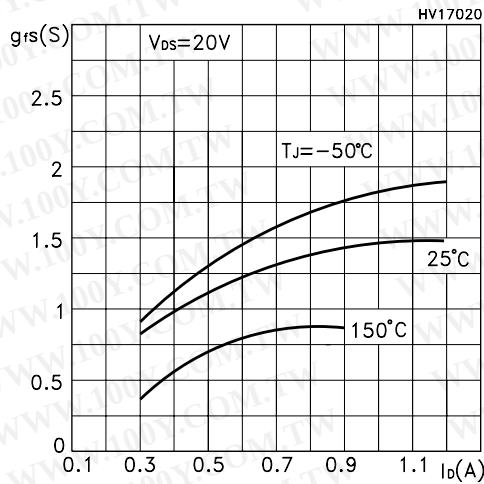


Figure 11: Capacitance Variations

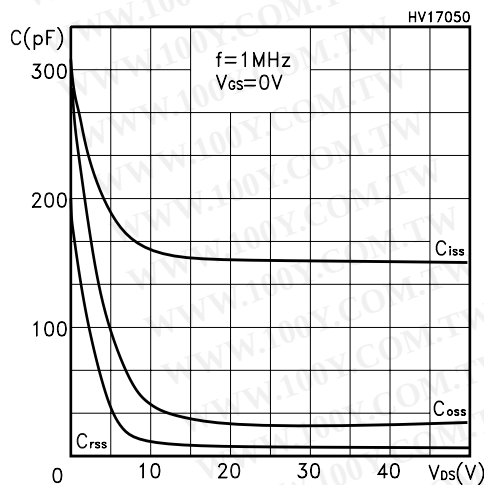


Figure 12: Transfer Characteristics

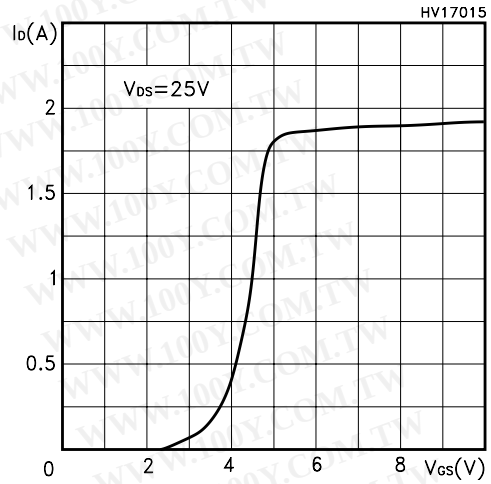


Figure 13: Gate Charge vs Gate-source Voltage

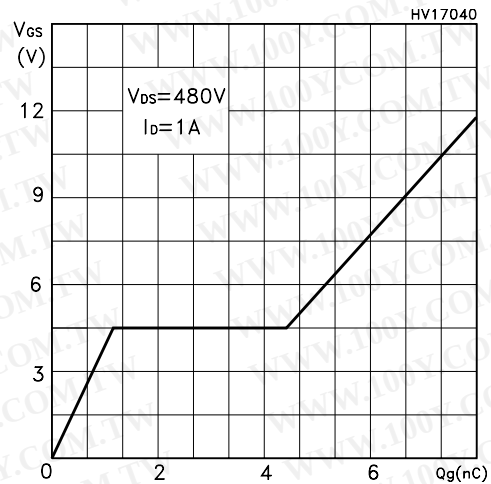


Figure 14: Static Drain-source On Resistance

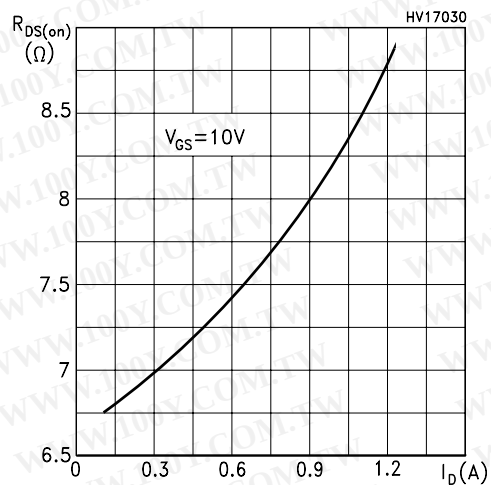


Figure 15: Normalized Gate Threshold Voltage vs Temperature

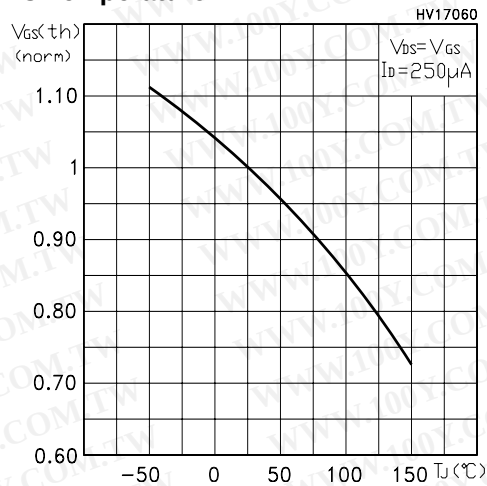


Figure 18: Normalized On Resistance vs Temperature

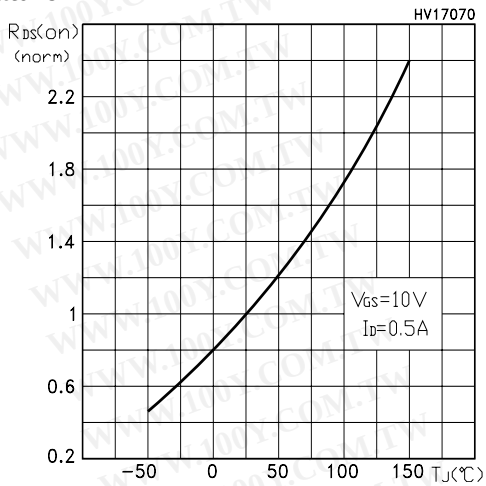


Figure 16: Source-Drain Forward Characteristics

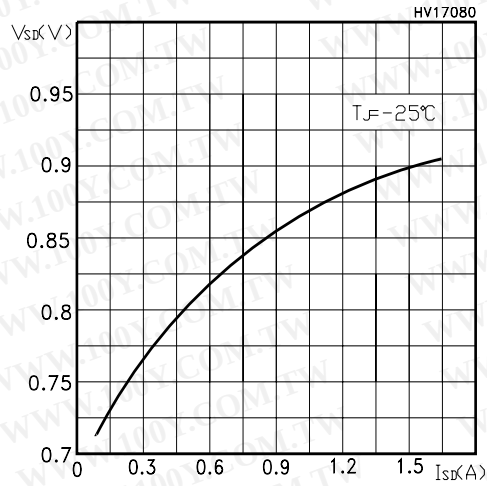


Figure 19: Normalized BV_{DSS} vs Temperature

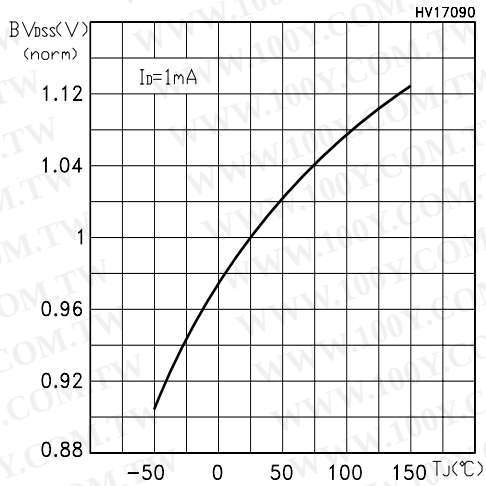


Figure 17: Maximum Avalanche Energy vs Temperature

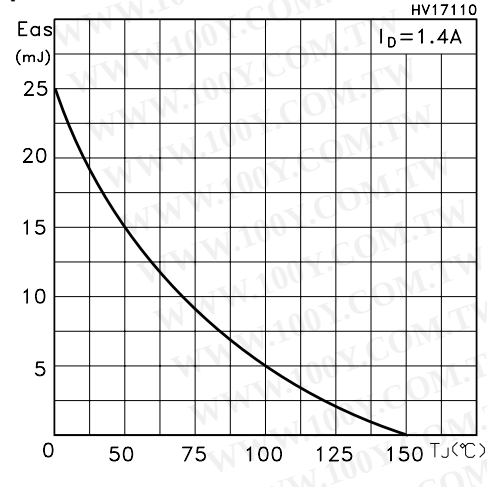


Figure 20: Max Id Current vs Tc

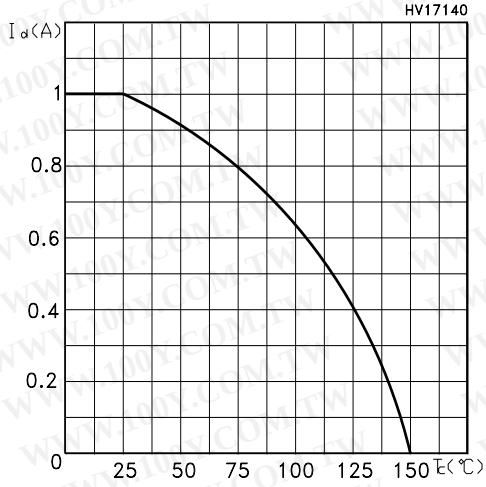


Figure 21: Switching Times Test Circuit For Resistive Load

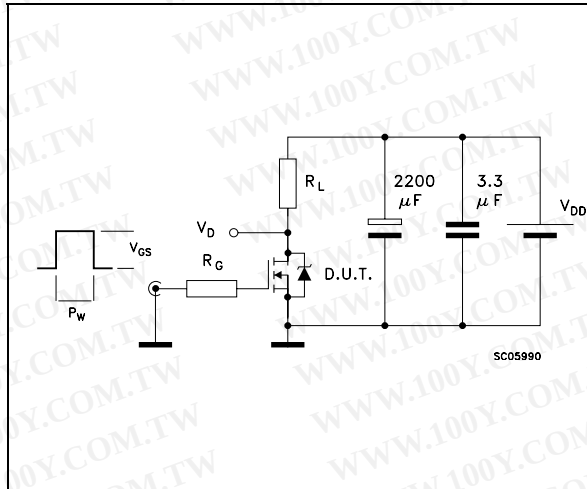


Figure 23: Gate Charge Test Circuit

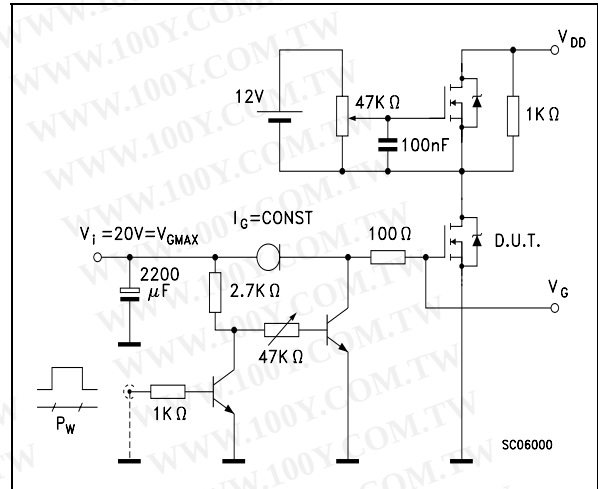
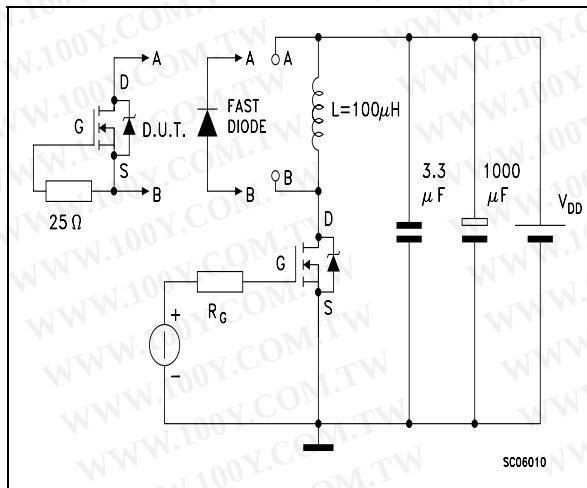


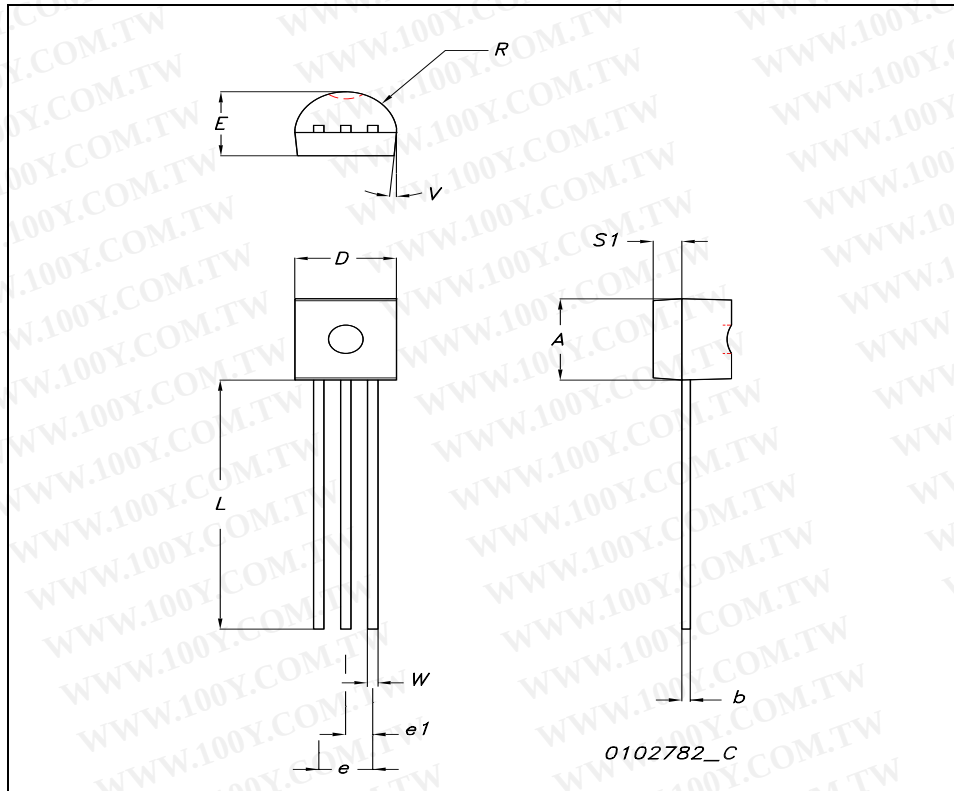
Figure 22: Test Circuit For Inductive Load Switching and Diode Recovery Times



STD1NK60 - STD1NK60-1 - STQ1HNK60R - STN1HNK60

TO-92 MECHANICAL DATA

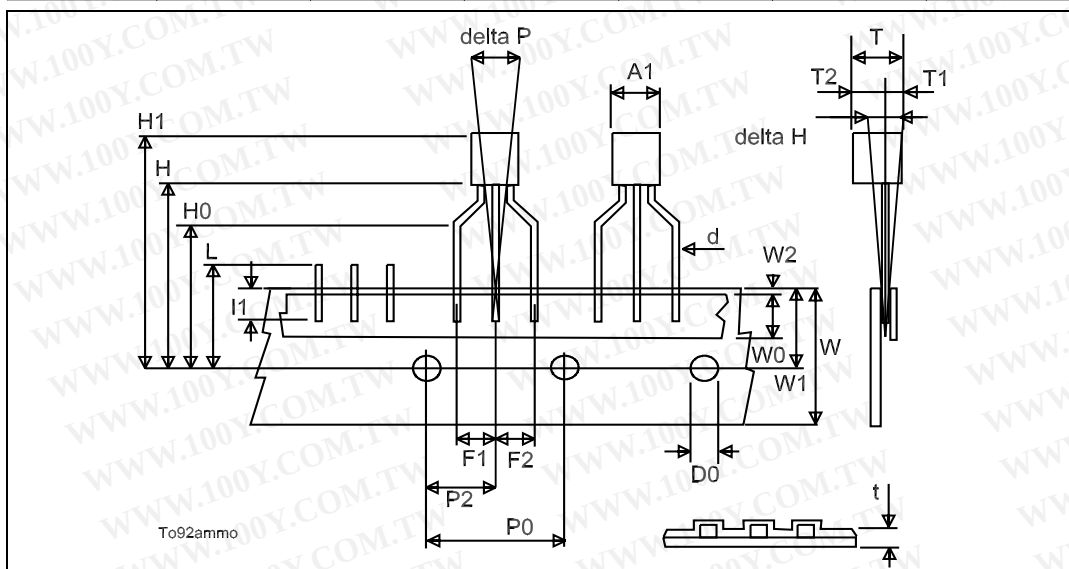
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.194
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.094		0.105
e1	1.14		1.40	0.044		0.055
L	12.70		15.49	0.50		0.610
R	2.16		2.41	0.085		0.094
S1	0.92		1.52	0.036		0.060
W	0.41		0.56	0.016		0.022
V		5°			5°	



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TO-92 AMMOPACK

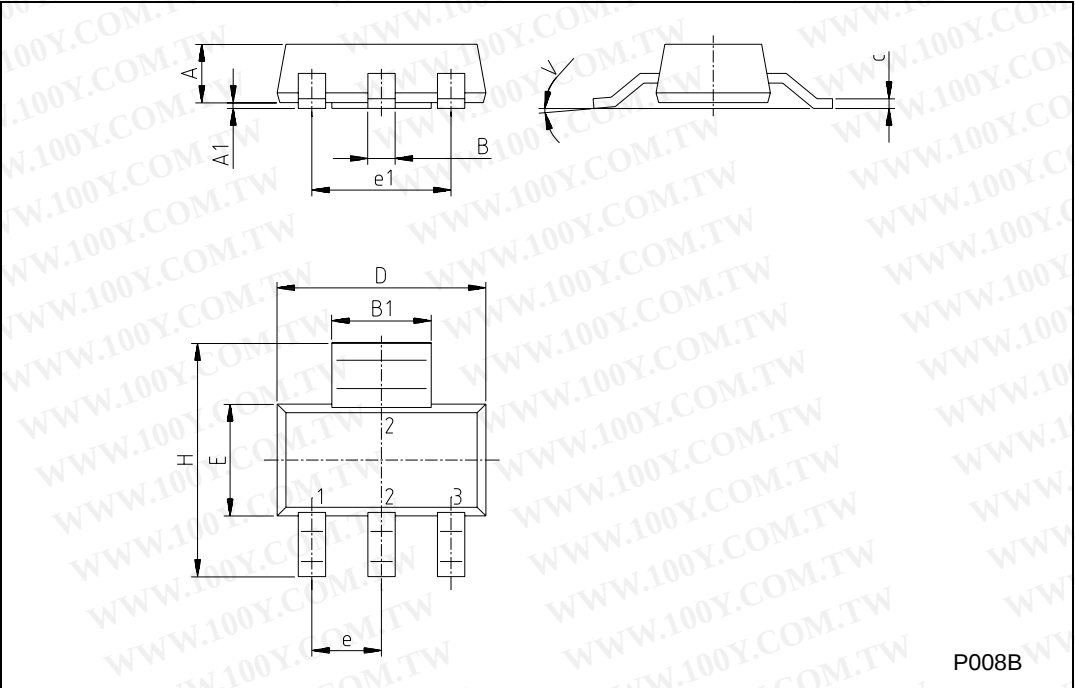
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1	4.45		4.95	0.170		0.194
T	3.30		3.94	0.130		0.155
T1			1.6			0.06
T2			2.3			0.09
d	0.41		0.56	0.016		0.022
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
l1	3			0.11		
delta P	-1		1	-0.04		0.04



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SOT-223 MECHANICAL DATA

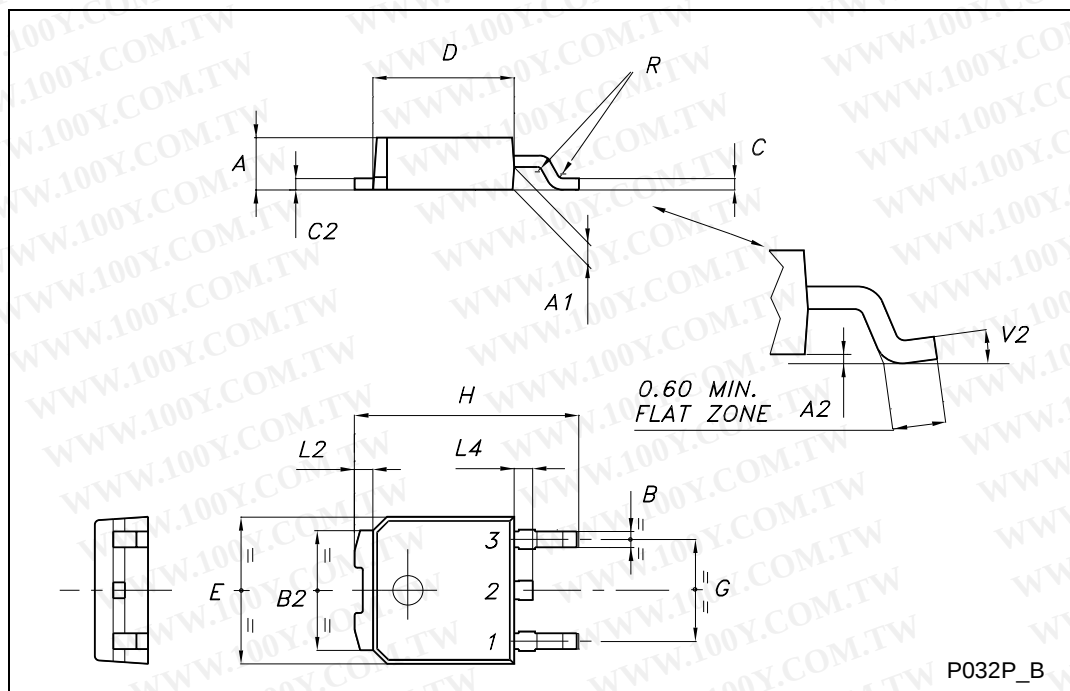
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



STD1NK60 - STD1NK60-1 - STQ1HNK60R - STN1HNK60

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

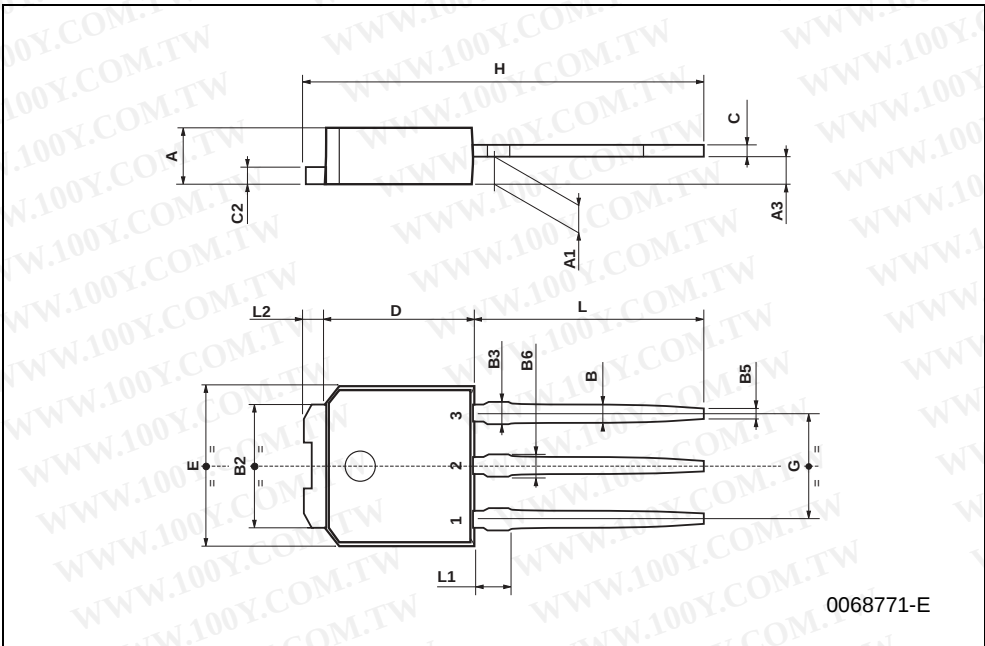


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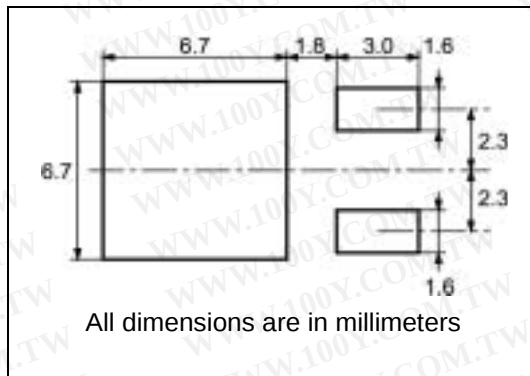
STD1NK60 - STD1NK60-1 - STQ1HNK60R - STN1HNK60

TO-251 (IPAK) MECHANICAL DATA

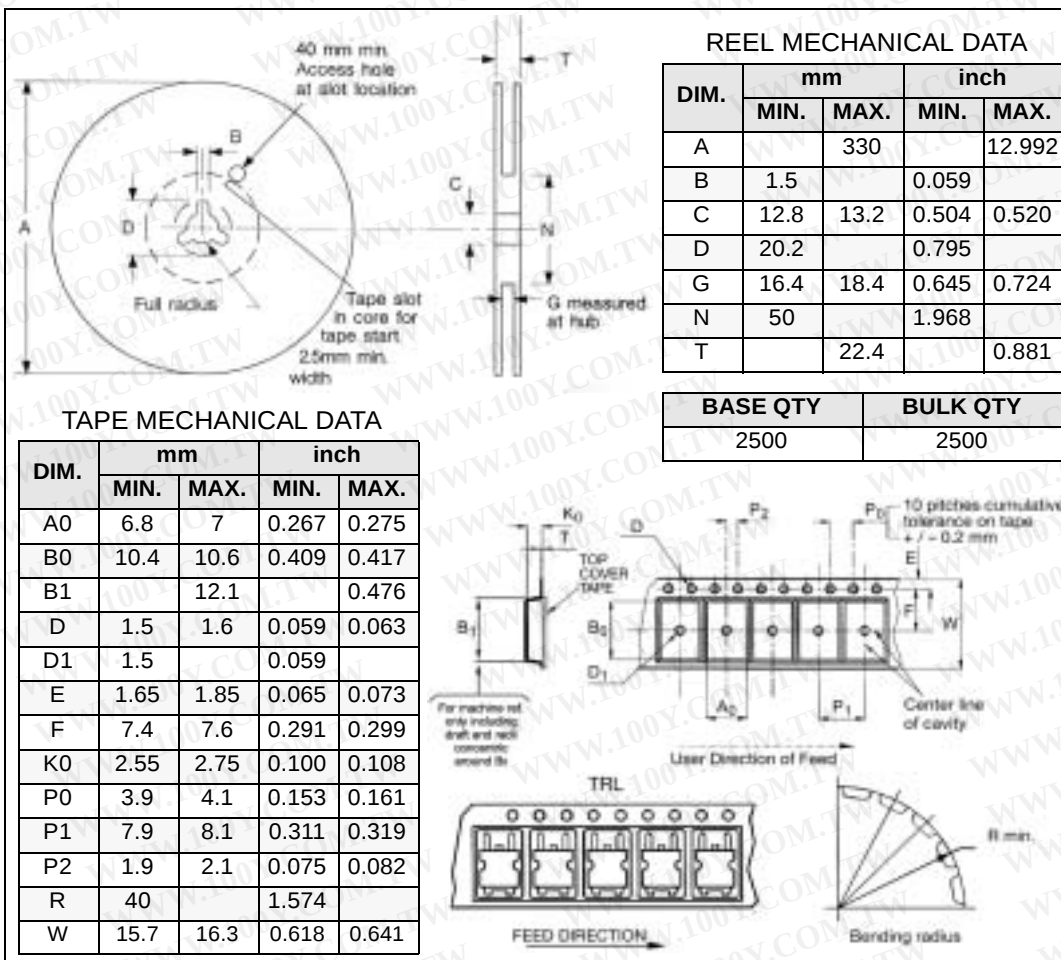
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



STD1NK60 - STD1NK60-1 - STQ1HNK60R - STN1HNK60

Table 9: Revision History

Date	Revision	Description of Changes
22-Nov-2004	2	Added SOT-223 Package and new stylesheet
14-Feb-2006	3	Modified marking on Table 2

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